



Fast Recovery Epitaxial Diode

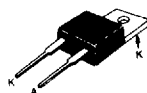
DSEI 8 $I_{FAV} = 8 \text{ A}$
 $V_{RRM} = 400\text{-}600 \text{ V}$
 $t_{rr} \leq 35 \text{ ns}$

V_{RSM}	V_{RRM}	Type
440	400	DSEI 8-04A
540	500	DSEI 8-05A
640	600	DSEI 8-06A



Symbol	Test conditions	Maximum ratings
I_{PRMS}	$T_{VJ} = T_{VJM}$	16 A
I_{FAVM}	1) $T_C = 115^\circ\text{C}$; rectangular; $\delta = 0.5$	8 A
I_{PRM}	$t_p < 10 \mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	130 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	100 A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	110 A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	85 A
	$t = 8.3 \text{ ms}$ (60 Hz), sine	95 A
$ di/dt $	$T_{VJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	50 A/s
	$t = 8.3 \text{ ms}$ (60 Hz), sine	50 A/s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine	36 A/s
	$t = 8.3 \text{ ms}$ (60 Hz), sine	37 A/s
T_{VJ}		40...+150 $^\circ\text{C}$
T_{VJM}		150 $^\circ\text{C}$
T_{stg}		40...+150 $^\circ\text{C}$
P_{tot}	$T_C = 115^\circ\text{C}$	14 W
M_s	Mounting torque	45-55 Ncm
Weight		2 g

TO-220 AC



A = Anode K = Cathode

Features

- International standard package
- Glass passivated chips
- Very short recovery time
- Extremely low losses at high switching frequencies
- Low I_{RM} -values
- Soft recovery behaviour

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Test conditions	typ.	Characteristics max.
I_R	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{PRM}$		0.5 mA
	$T_{VJ} = 25^\circ\text{C}$ $V_R = 0.8 \cdot V_{RRM}$		60 μA
	$T_{VJ} = 125^\circ\text{C}$ $V_R = 0.8 \cdot V_{PRM}$		1.5 mA
V_F	$I_F = 8 \text{ A}$; $T_{VJ} = 150^\circ\text{C}$		1.3 V
	$T_{VJ} = 25^\circ\text{C}$		1.5 V
V_{TO}	For power-loss calculations only		0.98 V
r_F	$T_{VJ} = T_{VJM}$		28.7 m Ω
R_{thJC}			2.5 K/W
R_{thJA}			60 K/W
t_{rr}	$I_F = 1 \text{ A}$; $di/dt = -15 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$		35 ns
I_{RM}	$V_A = 350 \text{ V}$; $I_F = 8 \text{ A}$; $di/dt = -64 \text{ A}/\mu\text{s}$	2.5	3.75 A
	$L \leq 0.05 \mu\text{H}$; $T_{VJ} = 100^\circ\text{C}$		

1) I_{FAVM} Rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $\delta = 0.5$
 Standards: DIN/IEC 747

DSEI 8, 400-600 V

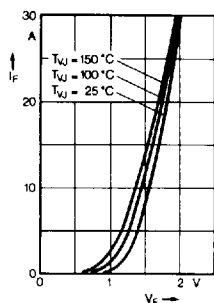


Fig. 1 Forward current versus voltage drop.

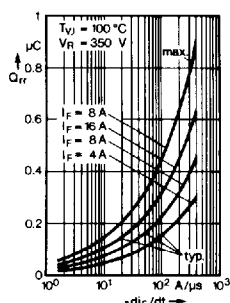
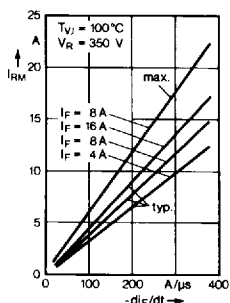
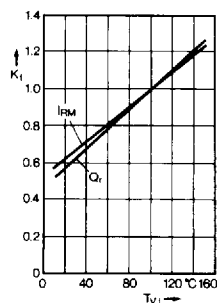

Fig. 2 Recovery charge versus $-di_F/dt$.

Fig. 3 Peak reverse current versus $-di_F/dt$.


Fig. 4 Dynamic parameters versus junction temperature.

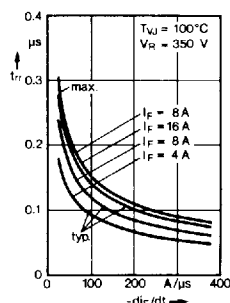
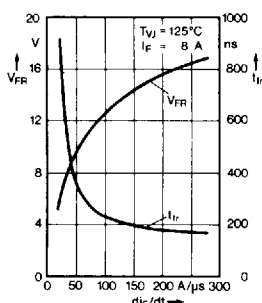
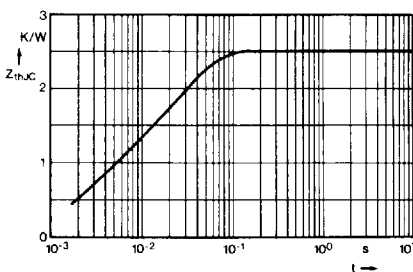
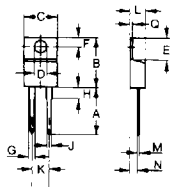

Fig. 5 Recovery time versus $-di_F/dt$.

Fig. 6 Peak forward voltage versus $-di_F/dt$.


Fig. 7 Transient thermal impedance junction to case.

Dimensions



Dim.	Millimeter	Max.	Min.	Max.
A	12.70	14.73	0.500	0.580
B	14.23	15.51	0.560	0.650
C	9.64	10.66	0.380	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.42	0.100	0.135
G	1.15	1.77	0.045	0.070
H	8.95	—	—	0.250
I	0.64	0.89	0.025	0.035
J	4.83	5.33	0.190	0.210
L	3.56	4.82	0.140	0.190
M	0.51	0.76	0.020	0.030
N	2.64	2.49	0.080	0.115
O	0.64	1.39	0.025	0.055